TOSHIBA TPS625,TPS626

TOSHIBA PHOTO DARLINGTON TRANSISTOR SILICON NPN EPITAXIAL PLANAR

TPS625, TPS626

OPTO-ELECTRONIC SWITCH HOME ELECTRIC EQUIPMENT OA EQUIPMENT

Small side view epoxy resin package

High sensitivity : TPS625 \cdots I_L=0.6mA (MIN.)

 $TPS626 \cdots I_L = 0.4 \text{mA (MIN.)}$

Half value angle : $\theta_{\frac{1}{2}} = \pm 15^{\circ} (TYP.)$

Visible light cut type (black package): TPS626

Optimum in combination with infrared LED TLN117 which has identical external dimensions.

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Emitter Voltage	v_{CEO}	30	V
Emitter-Collector Voltage	v_{ECO}	5	V
Collector Current	$I_{\mathbf{C}}$	40	mA
Collector Power Dissipation	$P_{\mathbf{C}}$	75	mW
Collector Power Dissipation Derating (Ta>25°C)	ΔP _C /°C	-1	mW/°C
Operating Temperature Range	Topr	-25~85	°C
Storage Temperature Range	$T_{ m stg}$	-40~100	°C
Soldering Temperature (5s)	T_{sol}	260 (Note 1)	°C

Note 1: Soldering portion of lead: above 2mm from the body of the device.

Unit in mm (): REFERENCE VALUE **JEDEC** EIAJ TOSHIBA

Weight: 0.1g (TYP.)

OPTO-ELECTRICAL CARACTERISTICS (Ta = 25°)

01 10 EEEE11116		1						
CHARACTERI	CHARACTERISTIC		TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Dark Current		I _D (I _{CEO})	$V_{CE} = 16V, E = 0$		_	0.03	0.25	μ A
Light Current		T_	$E = 0.1 \text{mW} / \text{cm}^2$	TPS625	0.6	2	_	mA
		$ ho_{ m L}$	$V_{CE} = 3V \text{ (Note 2, 3)}$	TPS626	0.4	1.4	_	
Collector-Emitter Saturation Voltage		V _{CE} (sat)	E=0.1mW/cm ² I _L = (Note 4)			0.9	1.2	V
Peak Sensitivity Wavelength		$\lambda_{\mathbf{p}}$		TPS625	_	820	_	nm
				TPS626	_	870	_	
Half Value Angle		$\theta_{\frac{1}{2}}$			_	±15	_	0
Switching Time	Rise Time	t_r	$V_{CC}=5V, I_{C}=10mA$		_	200	_	,,,
	Fall Time	t_f	$egin{array}{c} V_{CC} = 5V, I_C = 10 mA \\ R_L = 100 \Omega \end{array}$		_	150	_	μ s

Color temperature = 2870°K, Standard Tungsten Lamp

961001EAA2

TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.

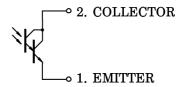
TOSHIBA TPS625,TPS626

Note 3. IL Classification

RANK	IL (mA)		
IMNIK	TPS625	TPS626	
(A)	0.6~3.6	0.4~2.4	
(B)	2.5~15	1.7~10.2	
(C)	5MIN.	3MIN.	
_	0.6MIN.	0.4MIN.	

Note 4. TPS625: 0.3mA, TPS626: 0.2mA

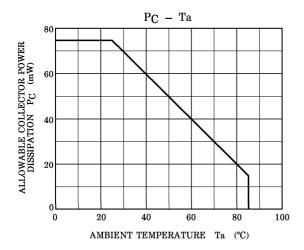
PIN CONNECTION

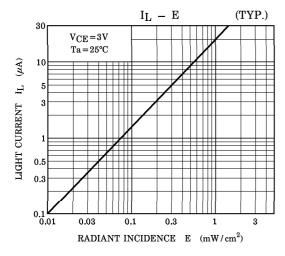


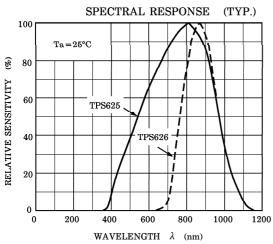
PRECAUTION

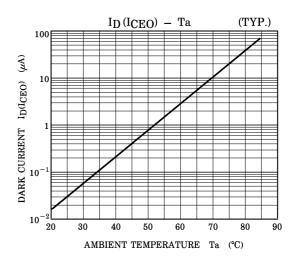
Please be careful of the followings.

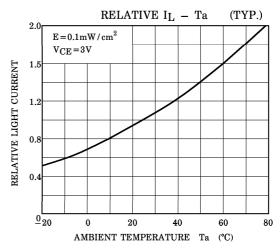
 When the lead is formed, the lead shall be formed at a distance of 2mm from the body without leaving forming stress to the body of the device.
 Soldering shall be performed after lead forming.



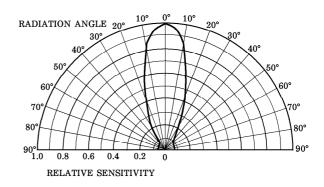












SWITCHING TIME TEST CIRCUIT

